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SN74LVC2T45DCUR

TI,Texas Instruments

Translation - Voltage Levels Dual-Bit Dual Supply Transceiver

SN74LVC2T45 Dual-Bit Dual-Supply Bus Transceiver With Configurable Voltage Translation

1 Features

- Fully Configurable Dual-Rail Design Allows Each Port to Operate Over the Full 1.65-V to 5.5-V Power-Supply Range
- V_{CC} Isolation Feature – If Either V_{CC} Input Is at GND, Both Ports Are in the High-Impedance State
- DIR Input Circuit Referenced to V_{CCA}
- Low Power Consumption, 4-μA Max I_{CC}
- Available in the Texas Instruments NanoFree™ Package
- ±24-mA Output Drive at 3.3 V
- I_{off} Supports Partial-Power-Down Mode Operation
- Max Data Rates
  - 420 Mbps (3.3-V to 5-V Translation)
  - 210 Mbps (Translate to 3.3 V)
  - 140 Mbps (Translate to 2.5 V)
  - 75 Mbps (Translate to 1.8 V)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 4000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

2 Applications

- Personal Electronic
- Industrial
- Enterprise
- Telecom

3 Description

This dual-bit noninverting bus transceiver uses two separate configurable power-supply rails. The A port is designed to track V_{CCA}. V_{CCA} accepts any supply voltage from 1.65 V to 5.5 V. The B port is designed to track V_{CCB}. V_{CCB} accepts any supply voltage from 1.65 V to 5.5 V. This allows for universal low-voltage bidirectional translation between any of the 1.8-V, 2.5-V, 3.3-V, and 5-V voltage nodes.

The SN74LVC2T45 is designed for asynchronous communication between two data buses. The logic levels of the direction-control (DIR) input activate either the B-port outputs or the A-port outputs. The device transmits data from the A bus to the B bus when the B-port outputs are activated, and from the B bus to the A bus when the A-port outputs are activated. The input circuitry on both A and B ports always is active and must have a logic HIGH or LOW level applied to prevent excess I_{CC} and I_{CCZ}.

The SN74LVC2T45 is designed so that the DIR input circuit is supplied by V_{CCA}. This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

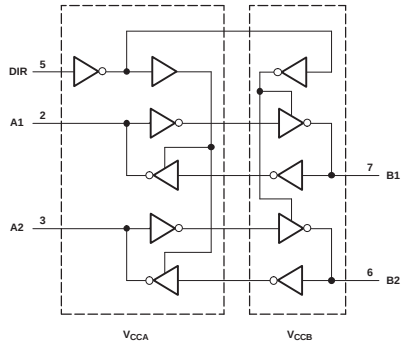
The V_{CC} isolation feature ensures that if either V_{CC} input is at GND, both ports are in the high-impedance state. NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Device Information[1]

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74LVC2T45DCT	SM8 (8)	2.95 mm x 2.80 mm
SN74LVC2T45DCU	VSSOP (8)	2.30 mm x 2.00 mm
SN74LVC2T45YZP	DSBGA (8)	1.89 mm x 0.89 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

Functional Block Diagram



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision J (October 2014) to Revision K — **Page**

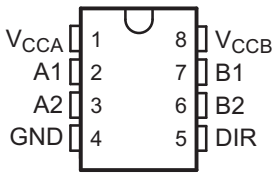
- Changed data sheet title ... 1
- Added Junction temperature, T_J in *Absolute Maximum Ratings* ... 4
- Added *Documentation Support*, *Receiving Notification of Documentation Updates* and *Community Resources* ... 19

Changes from Revision I (March 2007) to Revision J — **Page**

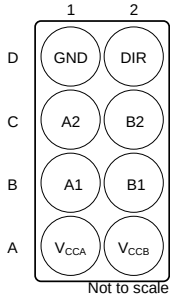
- Added *Pin Configuration and Functions* section, *ESD Ratings* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section ... 1

5 Pin Configuration and Functions

DCT or DCU Package
8-Pin SM8 or VSSOP
Top View



YZP Package
8-Pin DSGBA
Bottom View



Not to scale

Pin Functions: DCT, DCU

PIN		TYPE	DESCRIPTION
NO.	NAME		
1	V_{CCA}	P	A-port supply voltage. 1.65 V ≤ V_{CCA} ≤ 5.5 V
2	A1	I/O	Input/output A1. Referenced to V_{CCA}
3	A2	I/O	Input/output A2. Referenced to V_{CCA}
4	GND	G	Ground
5	DIR	I	Direction control signal
6	B2	I/O	Input/output B2. Referenced to V_{CCB}
7	B1	I/O	Input/output B1. Referenced to V_{CCB}
8	V_{CCB}	P	B-port supply voltage. 1.65 V ≤ V_{CCB} ≤ 5.5 V

Pin Functions: YZP

PIN		TYPE	DESCRIPTION
BALL	NAME		
A1	V_{CCA}	P	A-port supply voltage. 1.65 V ≤ V_{CCA} ≤ 5.5 V
A2	V_{CCB}	P	B-port supply voltage. 1.65 V ≤ V_{CCB} ≤ 5.5 V
B1	A1	I/O	Input/output A1. Referenced to V_{CCA}
B2	B1	I/O	Input/output B1. Referenced to V_{CCB}
C1	A2	I/O	Input/output A2. Referenced to V_{CCA}
C2	B2	I/O	Input/output B2. Referenced to V_{CCB}
D1	GND	G	Ground
D2	DIR	I	Direction control signal

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CCA} / V_{CCB}	Supply voltage		–0.5	6.5	V
V_I	Input voltage(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high-impedance or power-off state(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high or low state(2) (3)	A port	–0.5	V_{CCA} + 0.5	V
		B port	–0.5	V_{CCB} + 0.5	
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(3) The value of V_{CC} is provided in the recommended operating conditions table.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±4000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	
		Machine model (A115-A)	±200	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1) (2) (3)

			V_{CCI}	V_{CCO}	MIN	MAX	UNIT
V_{CCA} / V_{CCB}	Supply voltage				1.65	5.5	V
					1.65	5.5	
V_{IH}	High-level input voltage	Data inputs(4)	1.65 V to 1.95 V		V_{CCI} × 0.65		V
			2.3 V to 2.7 V		1.7		
			3 V to 3.6 V		2		
			4.5 V to 5.5 V		V_{CCI} × 0.7		
V_{IL}	Low-level input voltage	Data inputs(4)	1.65 V to 1.95 V			V_{CCI} × 0.35	V
			2.3 V to 2.7 V			0.7	
			3 V to 3.6 V			0.8	
			4.5 V to 5.5 V			V_{CCI} × 0.3	

(1) V_{CCI} is the V_{CC} associated with the input port.
(2) V_{CCO} is the V_{CC} associated with the output port.
(3) All unused data inputs of the device must be held at V_{CCI} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.
(4) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCI} × 0.7 V, V_{IL} max = V_{CCI} × 0.3 V.

Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)(1) (2) (3)

			V_{CCI}	V_{CCO}	MIN	MAX	UNIT
V_{IH}	High-level input voltage	DIR (referenced to V_{CCA})(5)	1.65 V to 1.95 V		V_{CCA} × 0.65		V
			2.3 V to 2.7 V		1.7		
			3 V to 3.6 V		2		
			4.5 V to 5.5 V		V_{CCA} × 0.7		
V_{IL}	Low-level input voltage	DIR (referenced to V_{CCA})(5)	1.65 V to 1.95 V			V_{CCA} × 0.35	V
			2.3 V to 2.7 V			0.7	
			3 V to 3.6 V			0.8	
			4.5 V to 5.5 V			V_{CCA} × 0.3	
V_I	Input voltage				0	5.5	V
V_O	Output voltage				0	V_{CCO}	V
I_{OH}	High-level output current			1.65 V to 1.95 V		–4	mA
				2.3 V to 2.7 V		–8	
				3 V to 3.6 V		–24	
				4.5 V to 5.5 V		–32	
I_{OL}	Low-level output current			1.65 V to 1.95 V		4	mA
				2.3 V to 2.7 V		8	
				3 V to 3.6 V		24	
				4.5 V to 5.5 V		32	
$\Delta t/\Delta v$	Input transition rise or fall rate	Data inputs	1.65 V to 1.95 V			20	ns/V
			2.3 V to 2.7 V			20	
			3 V to 3.6 V			10	
			4.5 V to 5.5 V			5	
		Control input	1.65 V to 5.5 V			5	
T_A	Operating free-air temperature				–40	85	°C

(5) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCA} × 0.7 V, V_{IL} max = V_{CCA} × 0.3 V.

6.4 Thermal Information

THERMAL METRIC(1)		SN74LVC2T45			UNIT
		DCT	DCU	YZP	
		8 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	184.0	203.6	105.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	114.7	75.9	1.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	96.4	82.3	10.8	°C/W
ψ_{JT}	Junction-to-top characterization parameter	40.8	7.2	3.1	°C/W
ψ_{JB}	Junction-to-board characterization parameter	95.4	81.9	10.8	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics[1][2]

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CCA}	V_{CCB}	T_A = 25°C			–40°C to +85°C		UNIT
						MIN	TYP	MAX	MIN	MAX	
V_{OH}		I_{OH} = –100 µA	$V_I = V_{IH}$	1.65 V to 4.5 V	1.65 V to 4.5 V				V_{CCO} – 0.1		V
		I_{OH} = –4 mA		1.65 V	1.65 V				1.2		
		I_{OH} = –8 mA		2.3 V	2.3 V				1.9		
		I_{OH} = –24 mA		3 V	3 V				2.4		
		I_{OH} = –32 mA		4.5 V	4.5 V				3.8		
V_{OL}		I_{OL} = 100 µA	$V_I = V_{IL}$	1.65 V to 4.5 V	1.65 V to 4.5 V					0.1	V
		I_{OL} = 4 mA		1.65 V	1.65 V					0.45	
		I_{OL} = 8 mA		2.3 V	2.3 V					0.3	
		I_{OL} = 24 mA		3 V	3 V					0.55	
		I_{OL} = 32 mA		4.5 V	4.5 V					0.55	
I_I	DIR	$V_I = V_{CCA}$ or GND		1.65 V to 5.5 V	1.65 V to 5.5 V			±1		±2	µA
I_{off}	A port	V_I or V_O = 0 to 5.5 V		0 V	0 to 5.5 V			±1		±2	µA
	B port			0 to 5.5 V	0 V			±1		±2	
I_{OZ}	A or B port	$V_O = V_{CCO}$ or GND		1.65 V to 5.5 V	1.65 V to 5.5 V			±1		±2	µA
I_{CCA}		$V_I = V_{CCI}$ or GND, I_O = 0		1.65 V to 5.5 V	1.65 V to 5.5 V					3	µA
				5 V	0 V					2	
				0 V	5 V					–2	
I_{CCB}		$V_I = V_{CCI}$ or GND, I_O = 0		1.65 V to 5.5 V	1.65 V to 5.5 V					3	µA
				5 V	0 V					–2	
				0 V	5 V					2	
$I_{CCA} + I_{CCB}$ (see Table 5)		$V_I = V_{CCI}$ or GND, I_O = 0		1.65 V to 5.5 V	1.65 V to 5.5 V					4	µA
ΔI_{CCA}	A port	One A port at V_{CCA} – 0.6 V, DIR at V_{CCA}, B port = open		3 V to 5.5 V	3 V to 5.5 V					50	µA
	DIR	DIR at V_{CCA} – 0.6 V, B port = open, A port at V_{CCA} or GND								50	
ΔI_{CCB}	B port	One B port at V_{CCB} – 0.6 V, DIR at GND, A port = open		3 V to 5.5 V	3 V to 5.5 V					50	µA
C_I	DIR	$V_I = V_{CCA}$ or GND		3.3 V	3.3 V		2.5				pF
C_{io}	A or B port	$V_O = V_{CCA/B}$ or GND		3.3 V	3.3 V		6				pF

(1) V_{CCO} is the V_{CC} associated with the output port.
(2) V_{CCI} is the V_{CC} associated with the input port.

6.6 Switching Characteristics: V_{CCA} = 1.8 V ± 0.15 V

over recommended operating free-air temperature range, V_{CCA} = 1.8 V ± 0.15 V (unless otherwise noted) (see Figure 17)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 1.8 V ±0.15 V		V_{CCB} = 2.5 V ±0.2 V		V_{CCB} = 3.3 V ±0.3 V		V_{CCB} = 5 V ±0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	3	17.7	2.2	10.3	1.7	8.3	1.4	7.2	ns
t_{PHL}			2.8	14.3	2.2	8.5	1.8	7.1	1.7	7	
t_{PLH}	B	A	3	17.7	2.3	16	2.1	15.5	1.9	15.1	ns
t_{PHL}			2.8	14.3	2.1	12.9	2	12.6	1.8	12.2	
t_{PHZ}	DIR	A	10.6	30.9	10.3	30.5	10.5	30.5	10.7	29.3	ns
t_{PLZ}			7.3	19.7	7.5	19.6	7.5	19.5	7	19.4	

Switching Characteristics: V_{CCA} = 1.8 V ± 0.15 V (continued)

over recommended operating free-air temperature range, V_{CCA} = 1.8 V ± 0.15 V (unless otherwise noted) (see Figure 17)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 1.8 V ±0.15 V		V_{CCB} = 2.5 V ±0.2 V		V_{CCB} = 3.3 V ±0.3 V		V_{CCB} = 5 V ±0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PHZ}	DIR	B	10	27.9	8.4	14.9	6.5	11.3	4.1	8.6	ns
t_{PLZ}			6.5	19.5	7.2	12.6	4.3	9.7	2.1	7.1	
t_{PZH} (1)	DIR	A		37.2		28.6		25.2		22.2	ns
t_{PZL} (1)				42.2		27.8		23.9		20.8	
t_{PZH} (1)	DIR	B		37.4		29.9		27.8		26.6	ns
t_{PZL} (1)				45.2		39		37.6		36.3	

(1) The enable time is a calculated value, derived using the formula shown in the *Enable Times* section.

6.7 Switching Characteristics: V_{CCA} = 2.5 V ± 0.2 V

over recommended operating free-air temperature range, V_{CCA} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 17)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 1.8 V ±0.15 V		V_{CCB} = 2.5 V ±0.2 V		V_{CCB} = 3.3 V ±0.3 V		V_{CCB} = 5 V ±0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	2.3	16	1.5	8.5	1.3	6.4	1.1	5.1	ns
t_{PHL}			2.1	12.9	1.4	7.5	1.3	5.4	0.9	4.6	
t_{PLH}	B	A	2.2	10.3	1.5	8.5	1.4	8	1	7.5	ns
t_{PHL}			2.2	8.5	1.4	7.5	1.3	7	0.9	6.2	
t_{PHZ}	DIR	A	6.6	17.1	7.1	16.8	6.8	16.8	5.2	16.5	ns
t_{PLZ}			5.3	12.6	5.2	12.5	4.9	12.3	4.8	12.3	
t_{PHZ}	DIR	B	10.7	27.9	8.1	13.9	5.8	10.5	3.5	7.6	ns
t_{PLZ}			7.8	18.9	6.2	11.2	3.6	8.9	1.4	6.2	
t_{PZH} (1)	DIR	A		29.2		19.7		16.9		13.7	ns
t_{PZL} (1)				36.4		21.4		17.5		13.8	
t_{PZH} (1)	DIR	B		28.6		21		18.7		17.4	ns
t_{PZL} (1)				30		24.3		22.2		21.1	

(1) The enable time is a calculated value, derived using the formula shown in the *Enable Times* section.

6.8 Switching Characteristics: V_{CCA} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range, V_{CCA} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 17)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 1.8 V ±0.15 V		V_{CCB} = 2.5 V ±0.2 V		V_{CCB} = 3.3 V ±0.3 V		V_{CCB} = 5 V ±0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	2.1	15.5	1.4	8	0.7	5.6	0.7	4.4	ns
t_{PHL}			2	12.6	1.3	7	0.8	5	0.7	4	
t_{PLH}	B	A	1.7	8.3	1.3	6.4	0.7	5.8	0.6	5.4	ns
t_{PHL}			1.8	7.1	1.3	5.4	0.8	5	0.7	4.5	
t_{PHZ}	DIR	A	5	10.9	5.1	10.8	5	10.8	5	10.4	ns
t_{PLZ}			3.4	8.4	3.7	8.4	3.9	8.1	3.3	7.8	
t_{PHZ}	DIR	B	11.2	27.3	8	13.7	5.8	10.4	2.9	7.4	ns
t_{PLZ}			9.4	17.7	5.6	11.3	4.3	8.3	1	5.6	
t_{PZH} (1)	DIR	A		26		17.7		14.1		11	ns
t_{PZL} (1)				34.4		19.1		15.4		11.9	

(1) The enable time is a calculated value, derived using the formula shown in the *Enable Times* section.

Switching Characteristics: V_{CCA} = 3.3 V ± 0.3 V (continued)

over recommended operating free-air temperature range, V_{CCA} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 17)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 1.8 V ±0.15 V		V_{CCB} = 2.5 V ±0.2 V		V_{CCB} = 3.3 V ±0.3 V		V_{CCB} = 5 V ±0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PZH} (1)	DIR	B		23.9		16.4		13.9		12.2	ns
t_{PZL} (1)				23.5		17.8		15.8		14.4	

6.9 Switching Characteristics: V_{CCA} = 5 V ± 0.5 V

over recommended operating free-air temperature range, V_{CCA} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 17)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 1.8 V ±0.15 V		V_{CCB} = 2.5 V ±0.2 V		V_{CCB} = 3.3 V ±0.3 V		V_{CCB} = 5 V ±0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	1.9	15.1	1	7.5	0.6	5.4	0.5	3.9	ns
t_{PHL}			1.8	12.2	0.9	6.2	0.7	4.5	0.5	3.5	
t_{PLH}	B	A	1.4	7.2	1	5.1	0.7	4.4	0.5	3.9	ns
t_{PHL}			1.7	7	0.9	4.6	0.7	4	0.5	3.5	
t_{PHZ}	DIR	A	2.9	8.2	2.9	7.9	2.8	7.9	2.2	7.8	ns
t_{PLZ}			1.4	6.9	1.3	6.7	0.7	6.7	0.7	6.6	
t_{PHZ}	DIR	B	11.2	26.1	7.2	13.9	5.8	10.1	1.3	7.3	ns
t_{PLZ}			8.4	16.9	5	11	4	7.7	1	5.6	
t_{PZH} (1)	DIR	A		24.1		16.1		12.1		9.5	ns
t_{PZL} (1)				33.1		18.5		14.1		10.8	
t_{PZH} (1)	DIR	B		22		14.2		12.1		10.5	ns
t_{PZL} (1)				20.4		14.1		12.4		11.3	

(1) The enable time is a calculated value, derived using the formula shown in the *Enable Times* section.

6.10 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CCA} = V_{CCB} = 1.8 V	V_{CCA} = V_{CCB} = 2.5 V	V_{CCA} = V_{CCB} = 3.3 V	V_{CCA} = V_{CCB} = 5 V	UNIT
			TYP	TYP	TYP	TYP	
C_{pdA} (1)	A-port input, B-port output	C_L = 0 pF, f = 10 MHz, $t_r = t_f$ = 1 ns	3	4	4	4	pF
	B-port input, A-port output		18	19	20	21	
C_{pdB} (1)	A-port input, B-port output	C_L = 0 pF, f = 10 MHz, $t_r = t_f$ = 1 ns	18	19	20	21	pF
	B-port input, A-port output		3	4	4	4	

(1) Power dissipation capacitance per transceiver

6.11 Typical Characteristics

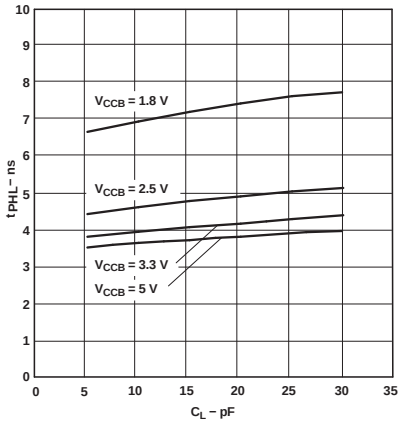


Figure 1. Typical Propagation Delay of High-to-Low (A to B) vs Load Capacitance T_A = 25°C, V_{CCA} = 1.8 V

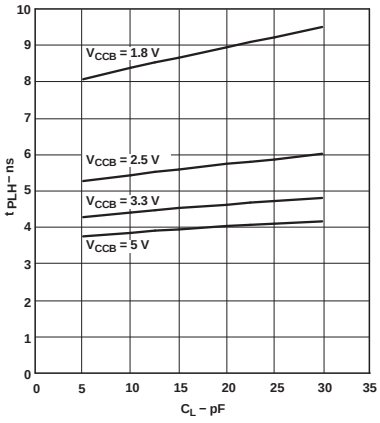


Figure 2. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance T_A = 25°C, V_{CCA} = 1.8 V

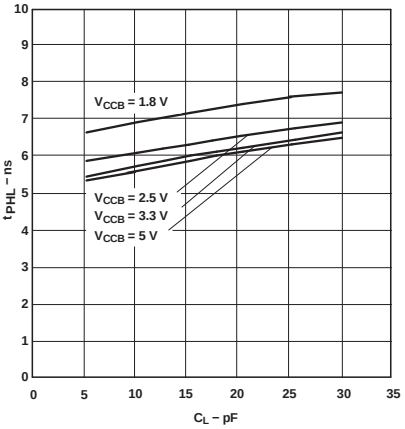


Figure 3. Typical Propagation Delay of High-to-Low (B to A) vs Load Capacitance T_A = 25°C, V_{CCA} = 1.8 V

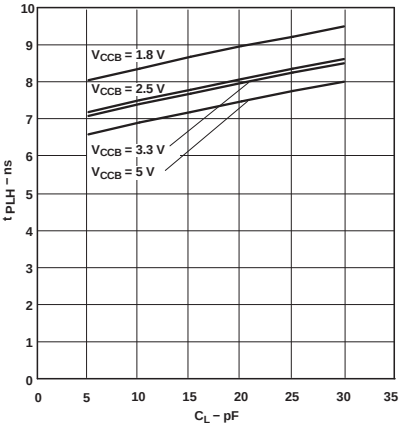


Figure 4. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance T_A = 25°C, V_{CCA} = 1.8 V

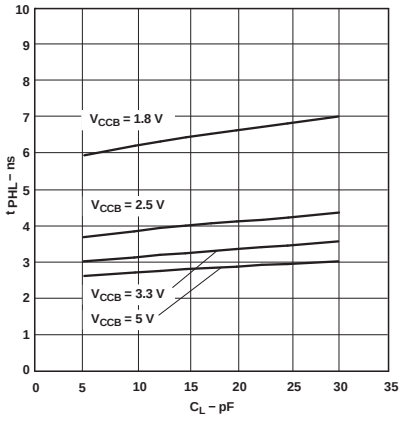


Figure 5. Typical Propagation Delay of High-to-Low (A to B) vs Load Capacitance T_A = 25°C, V_{CCA} = 2.5 V

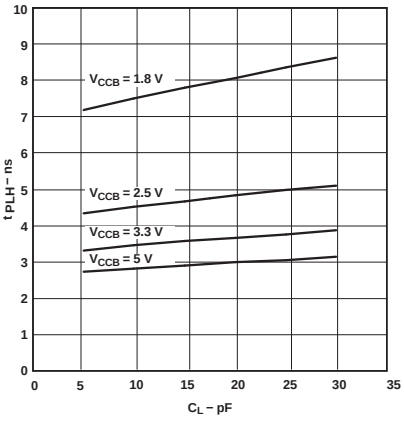


Figure 6. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance T_A = 25°C, V_{CCA} = 2.5 V

Typical Characteristics (continued)

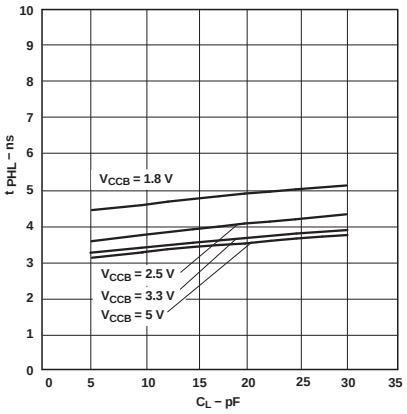


Figure 7. Typical Propagation Delay of High-to-Low (B to A) vs Load Capacitance T_A = 25°C, V_{CCA} = 2.5 V

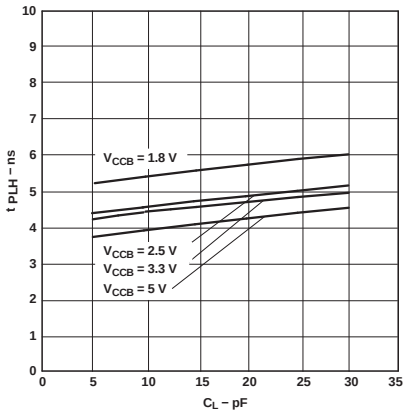


Figure 8. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance T_A = 25°C, V_{CCA} = 2.5 V

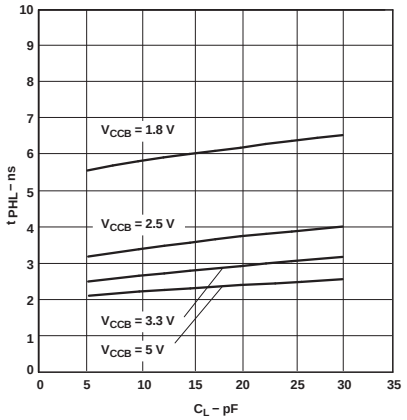


Figure 9. Typical Propagation Delay of High-to-Low (A to B) vs Load Capacitance T_A = 25°C, V_{CCA} = 3.3 V

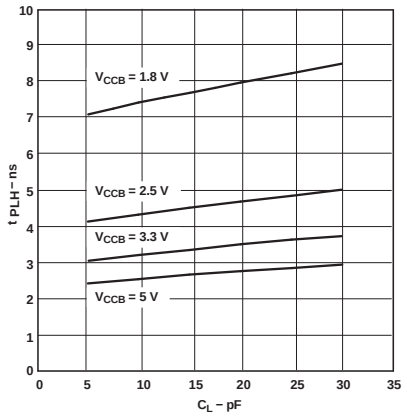


Figure 10. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance T_A = 25°C, V_{CCA} = 3.3 V

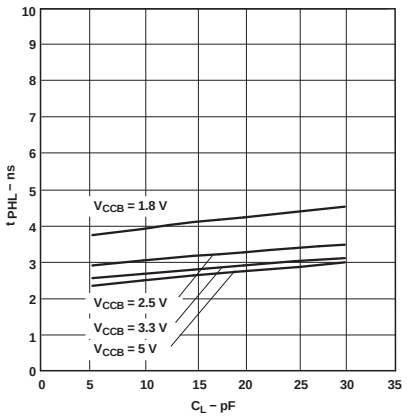


Figure 11. Typical Propagation Delay of High-to-Low (B to A) vs Load Capacitance T_A = 25°C, V_{CCA} = 3.3 V

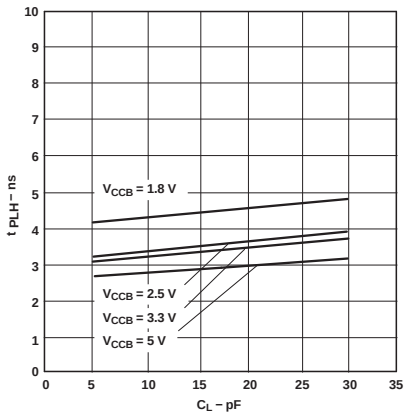


Figure 12. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance T_A = 25°C, V_{CCA} = 3.3 V

Typical Characteristics (continued)

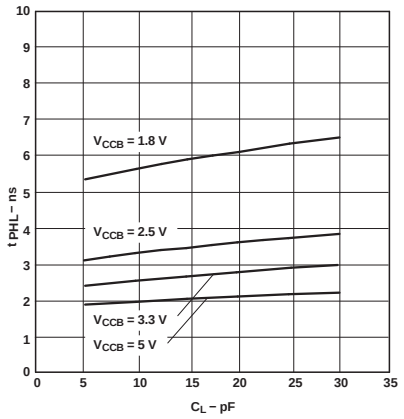


Figure 13. Typical Propagation Delay of High-to-Low (A to B) vs Load Capacitance T_A = 25°C, V_{CCA} = 5 V

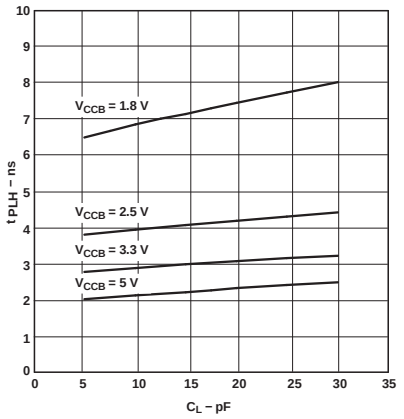


Figure 14. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance T_A = 25°C, V_{CCA} = 5 V

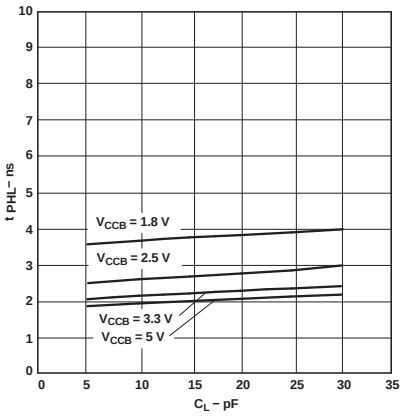


Figure 15. Typical Propagation Delay of High-to-Low (B to A) vs Load Capacitance T_A = 25°C, V_{CCA} = 5 V

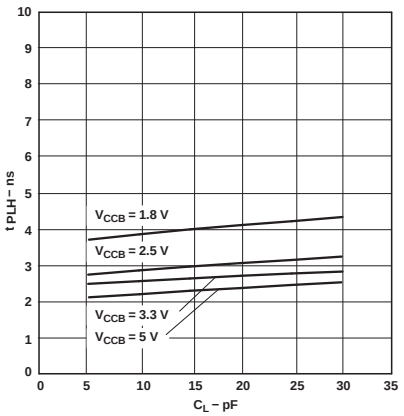
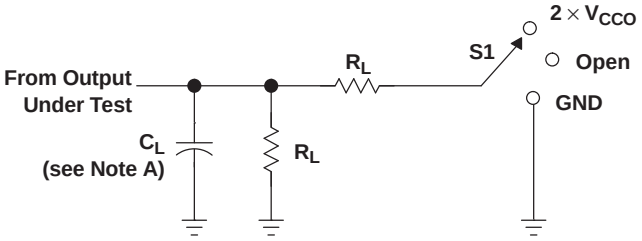


Figure 16. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance T_A = 25°C, V_{CCA} = 5 V

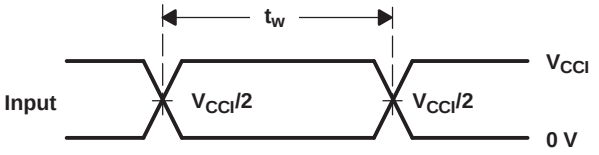
7 Parameter Measurement Information



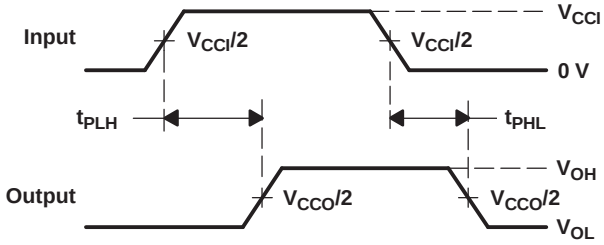
LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CCO}$
t_{PHZ}/t_{PZH}	GND

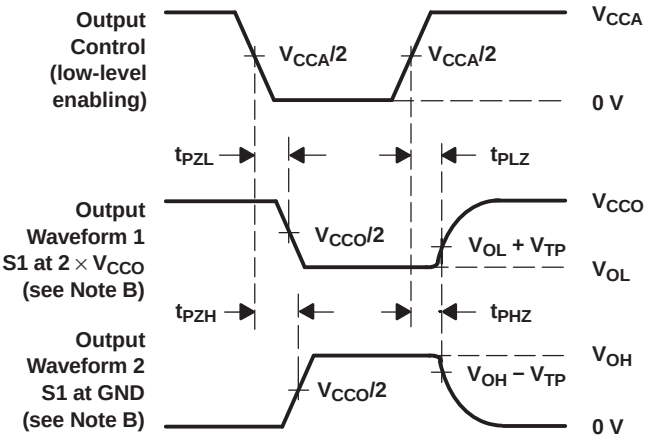
V_{CCO}	C_L	R_L	V_{TP}
1.8 V ± 0.15 V	15 pF	2 kΩ	0.15 V
2.5 V ± 0.2 V	15 pF	2 kΩ	0.15 V
3.3 V ± 0.3 V	15 pF	2 kΩ	0.3 V
5 V ± 0.5 V	15 pF	2 kΩ	0.3 V



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES:
A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, dv/dt ≥ 1 V/ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. V_{CCI} is the V_{CC} associated with the input port.
I. V_{CCO} is the V_{CC} associated with the output port.
J. All parameters and waveforms are not applicable to all devices.

Figure 17. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LVC2T45 is dual-bit, dual-supply noninverting voltage level translation. Pin Ax and direction control pin are support by V_{CCA} and pin Bx are support by V_{CCB}. The A port is able to accept I/O voltages ranging from 1.65 V to 5.5 V, while the B port can accept I/O voltages from 1.65 V to 5.5 V. The high on DIR allows data transmission from A to B and a low on DIR allows data transmission from B to A.

8.2 Functional Block Diagram

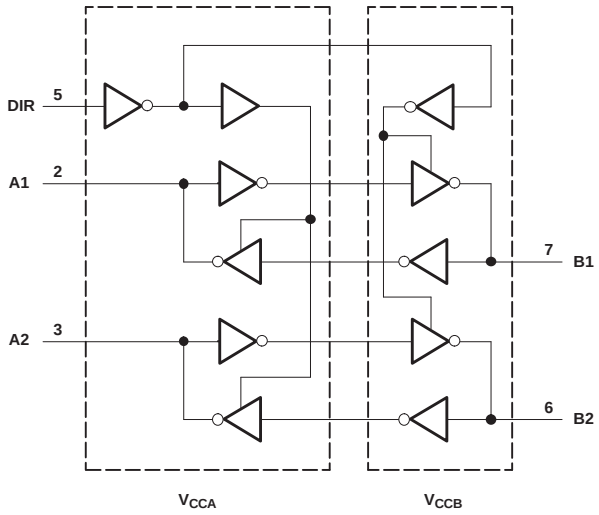


Figure 18. Logic Diagram (Positive Logic)

8.3 Feature Description

8.3.1 Fully Configurable Dual-Rail Design Allows Each Port to Operate Over the Full 1.65-V to 5.5-V Power-Supply Range

Both V_{CCA} and V_{CCB} can be supplied at any voltage between 1.65 V and 5.5 V making the device suitable for translating between any of the voltage nodes (1.8-V, 2.5-V, 3.3-V and 5-V).

8.3.2 Support High-Speed Translation

SN74LVC2T45 can support high data rate application. The translated signal data rate can be up to 420 Mbps when signal is translated from 3.3 V to 5 V.

8.3.3 I_{off} Supports Partial-Power-Down Mode Operation

I_{off} will prevent backflow current by disabling I/O output circuits when device is in partial-power-down mode.

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74LVC2T45 device.

Table 1. Function Table(1) (Each Transceiver)

INPUT DIR	OPERATION
L	B data to A bus
H	A data to B bus

(1) Input circuits of the data I/Os always are active.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC2T45 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The maximum data rate can be up to 420 Mbps when device translate signal from 3.3 V to 5 V.

9.2 Typical Applications

9.2.1 Unidirectional Logic Level-Shifting Application

Figure 19 shows an example of the SN74LVC2T45 being used in a unidirectional logic level-shifting application.

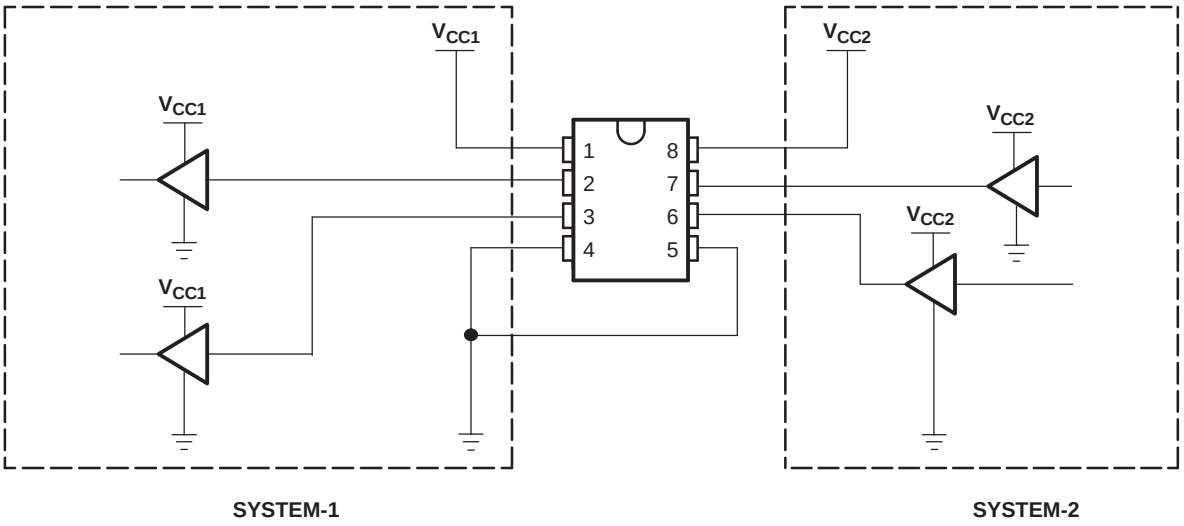


Figure 19. Unidirectional Logic Level-Shifting Application

9.2.1.1 Design Requirements

Table 2 lists the pins and pin descriptions of the SN74LVC2T45 connections with SYSTEM-1 and SYSTEM-2.

Table 2. SN74LVC2T45 Pin Connections With SYSTEM-1 and SYSTEM-2

PIN	NAME	FUNCTION	DESCRIPTION
1	V_{CCA}	V_{CC1}	SYSTEM-1 supply voltage (1.65 V to 5.5 V)
2	A1	OUT1	Output level depends on V_{CC1} voltage.
3	A2	OUT2	Output level depends on V_{CC1} voltage.
4	GND	GND	Device GND
5	DIR	DIR	GND (low level) determines B-port to A-port direction.
6	B2	IN2	Input threshold value depends on V_{CC2} voltage.
7	B1	IN1	Input threshold value depends on V_{CC2} voltage.
8	V_{CCB}	V_{CC2}	SYSTEM-2 supply voltage (1.65 V to 5.5 V)

For this design example, use the parameters listed in Table 3.

Table 3. Design Parameters

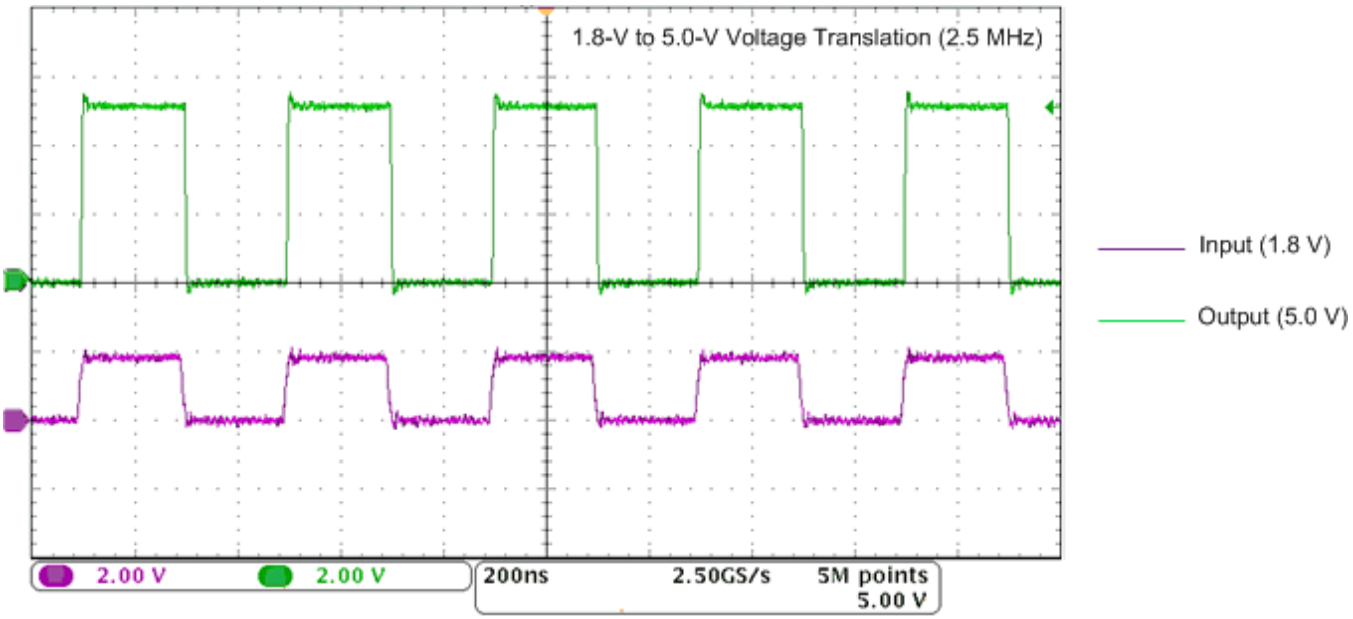
DESIGN PARAMETER	EXAMPLE VALUE
Input voltage range	1.65 V to 5.5 V
Output voltage range	1.65 V to 5.5 V

9.2.1.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
  - Use the supply voltage of the device that is driving the SN74LVC2T45 device to determine the input voltage range. For a valid logic high the value must exceed the V_{IH} of the input port. For a valid logic low the value must be less than the V_{IL} of the input port.
- Output voltage range
  - Use the supply voltage of the device that the SN74LVC2T45 device is driving to determine the output voltage range.

9.2.1.3 Application Curve



9.2.2 Bidirectional Logic Level-Shifting Application

Figure 20 shows the SN74LVC2T45 being used in a bidirectional logic level-shifting application. Because the SN74LVC2T45 does not have an output-enable (OE) pin, the system designer should take precautions to avoid bus contention between SYSTEM-1 and SYSTEM-2 when changing directions.

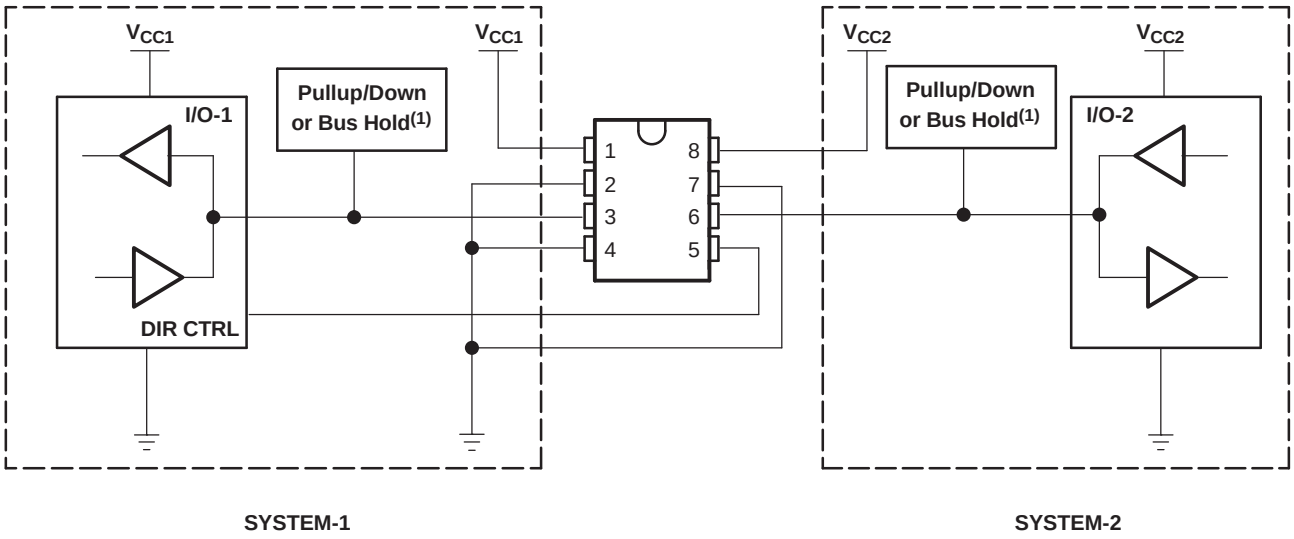


Figure 20. Bidirectional Logic Level-Shifting Application

9.2.2.1 Design Requirements

Please refer to *Unidirectional Logic Level-Shifting Application*.

9.2.2.2 Detailed Design Procedure

Table 4 shows data transmission from SYSTEM-1 to SYSTEM-2 and then from SYSTEM-2 to SYSTEM-1.

Table 4. Data Transmission Sequence

STATE	DIR CTRL	I/O-1	I/O-2	DESCRIPTION
1	H	Out	In	SYSTEM-1 data to SYSTEM-2
2	H	Hi-Z	Hi-Z	SYSTEM-2 is getting ready to send data to SYSTEM-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on pullup or pulldown.(1)
3	L	Hi-Z	Hi-Z	DIR bit is flipped. I/O-1 and I/O-2 still are disabled. The bus-line state depends on pullup or pulldown.(1)
4	L	In	Out	SYSTEM-2 data to SYSTEM-1

(1) SYSTEM-1 and SYSTEM-2 must use the same conditions, that is, both pullup or both pulldown.

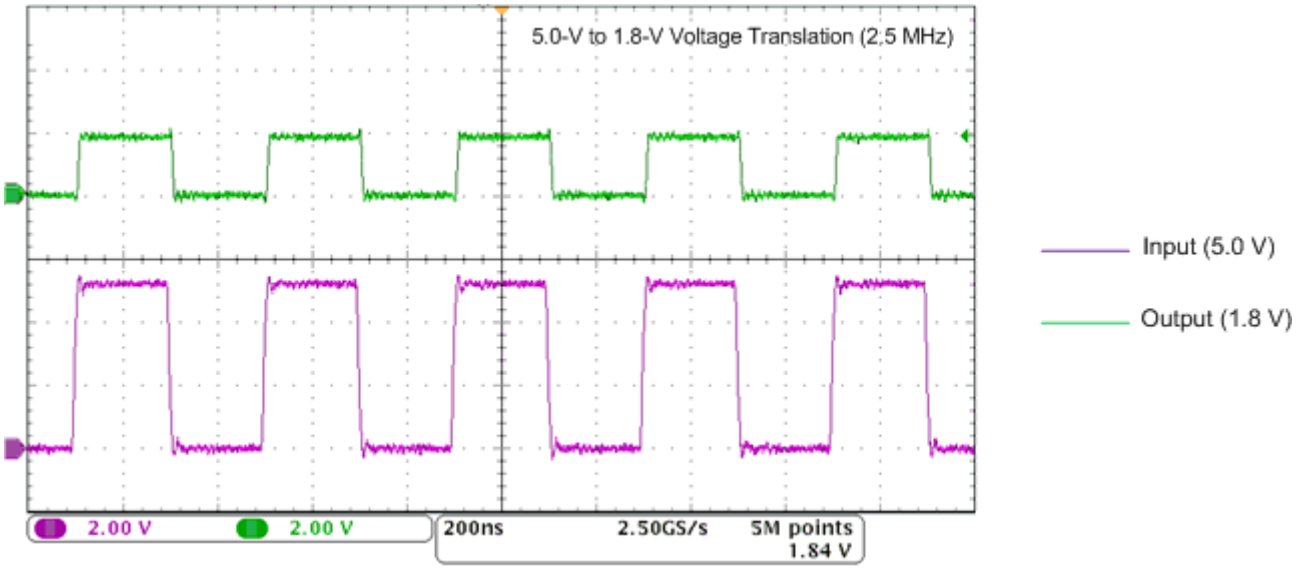
9.2.2.2.1 Enable Times

Calculate the enable times for the SN74LVC2T45 using the following formulas:

- t_{PZH} (DIR to A) = t_{PLZ} (DIR to B) + t_{PLH} (B to A)
- t_{PZL} (DIR to A) = t_{PHZ} (DIR to B) + t_{PHL} (B to A)
- t_{PZH} (DIR to B) = t_{PLZ} (DIR to A) + t_{PLH} (A to B)
- t_{PZL} (DIR to B) = t_{PHZ} (DIR to A) + t_{PHL} (A to B)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the SN74LVC2T45 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

9.2.2.3 Application Curve



10 Power Supply Recommendations

10.1 Power-Up Considerations

A proper power-up sequence with inputs held at ground should be followed as listed :

1. Connect ground before any supply voltage is applied.
2. Power up V_{CCA}.
3. V_{CCB} can be ramped up along with or after V_{CCA}.

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions* table.

Each V_{CC} pin must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 µF is recommended. If there are multiple V_{CC} pins, 0.01 µF or 0.022 µF is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1-µF and 1-µF are commonly used in parallel. The bypass capacitor must be installed as close to the power pin as possible for best results.

Table 5. Typical Total Static Power Consumption (I_{CCA} + I_{CCB})

V_{CCB}	V_{CCA}					UNIT
	0 V	1.8 V	2.5 V	3.3 V	5 V	
0 V	0	<1	<1	<1	<1	µA
1.8 V	<1	<2	<2	<2	2	
2.5 V	<1	<2	<2	<2	<2	
3.3 V	<1	<2	<2	<2	<2	
5 V	<1	2	<2	<2	<2	

11 Layout

11.1 Layout Guidelines

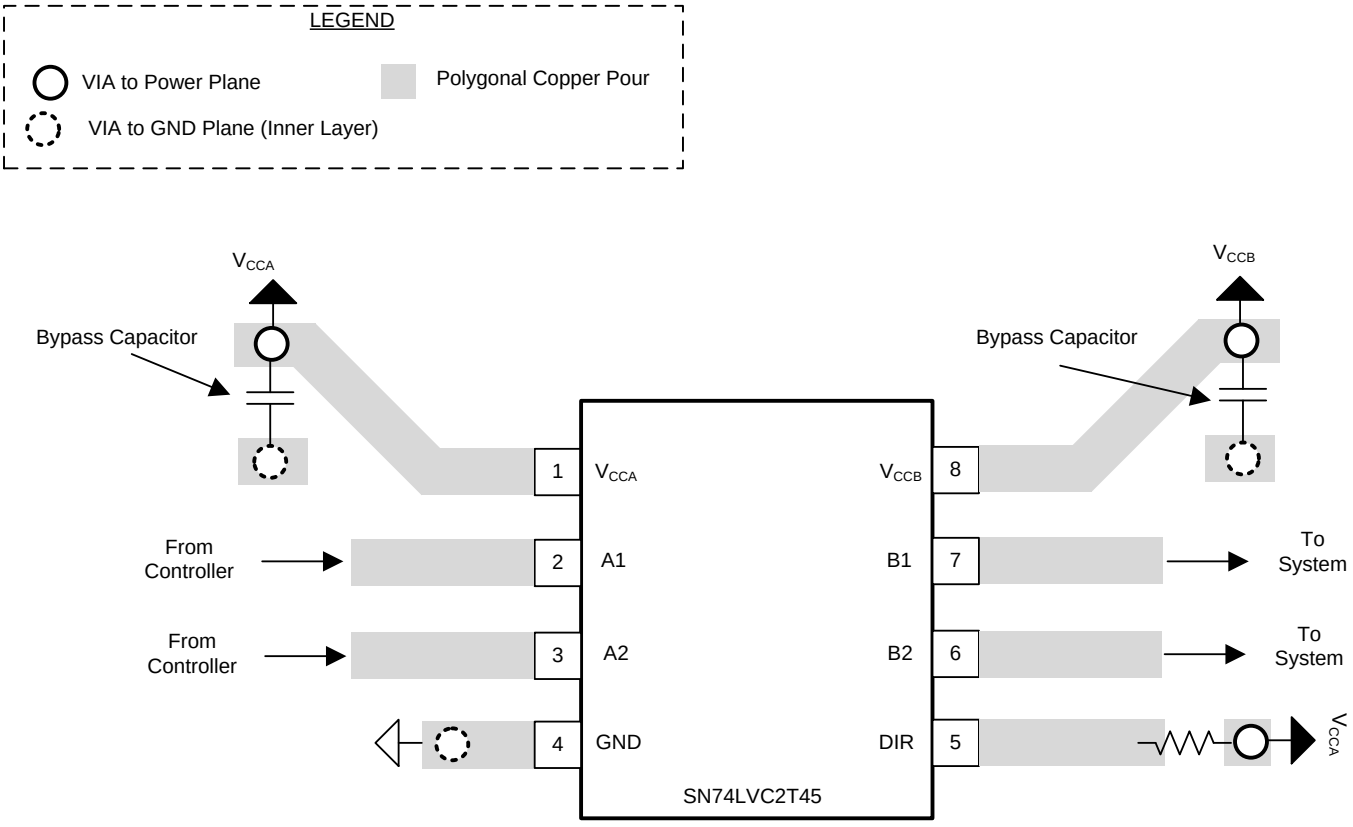
To ensure reliability of the device, following common printed-circuit board layout guidelines is recommended.

- Bypass capacitors should be used on power supplies.
- Short trace lengths should be used to avoid excessive loading.

Layout Guidelines (continued)

- Placing pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depending on the system requirements

11.2 Layout Example



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004.

Designing with SN74LVCXT245 and SN74LVCHXT245 Family of Direction controlled voltage translators,SLVA746

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

NanoFree, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	O
SN74LVC2T45DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	
SN74LVC2T45DCTRE4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	
SN74LVC2T45DCTT	ACTIVE	SM8	DCT	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	
SN74LVC2T45DCTTG4	ACTIVE	SM8	DCT	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	
SN74LVC2T45DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	
SN74LVC2T45DCURE4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	
SN74LVC2T45DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	
SN74LVC2T45DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	
SN74LVC2T45DCUTG4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	
SN74LVC2T45YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SAC396 | SNAGCU	Level-1-260C-UNLIM	

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including t
do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in sp
reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm
flame retardants must also meet the <=1000ppm threshold requirement.

www.ti.com

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a li
of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/B
lines if the finish value exceeds the maximum column width.

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provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate informatio
continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis o
TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer o

OTHER QUALIFIED VERSIONS OF SN74LVC2T45 :

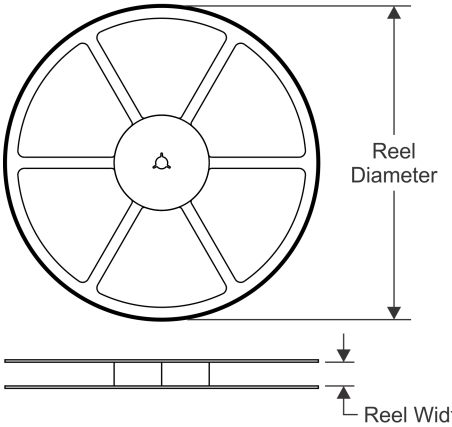
- Automotive: SN74LVC2T45-Q1
- Enhanced Product: SN74LVC2T45-EP

NOTE: Qualified Version Definitions:

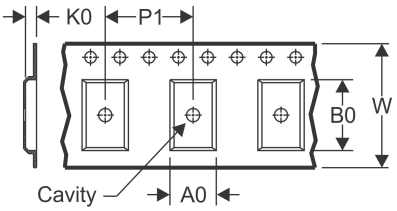
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS

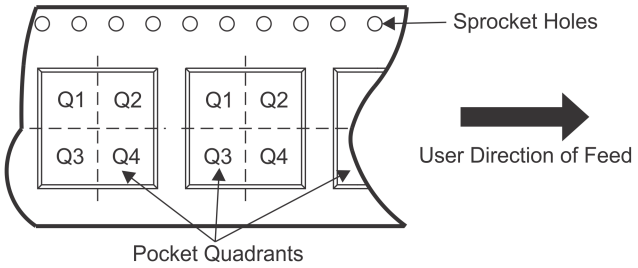


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

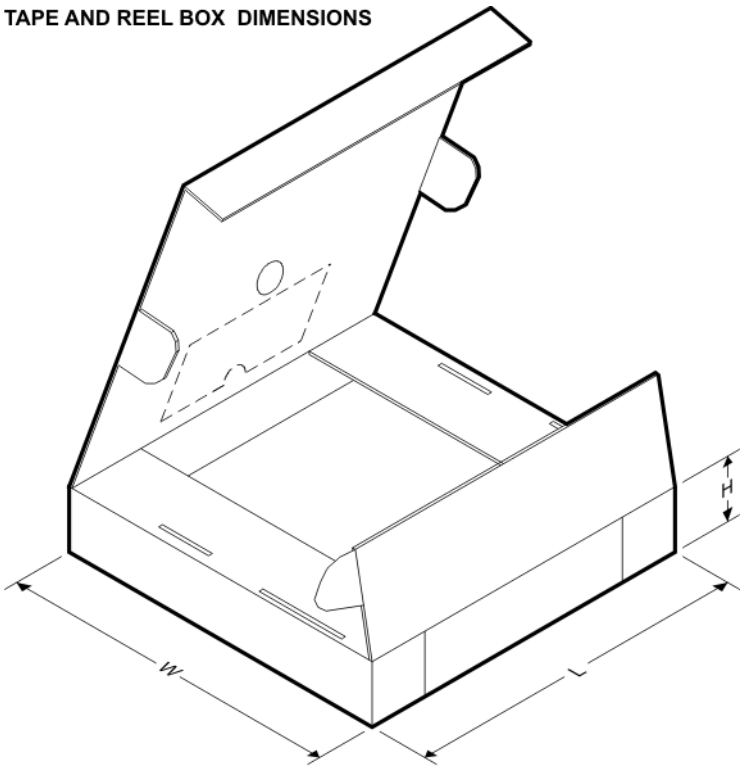
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

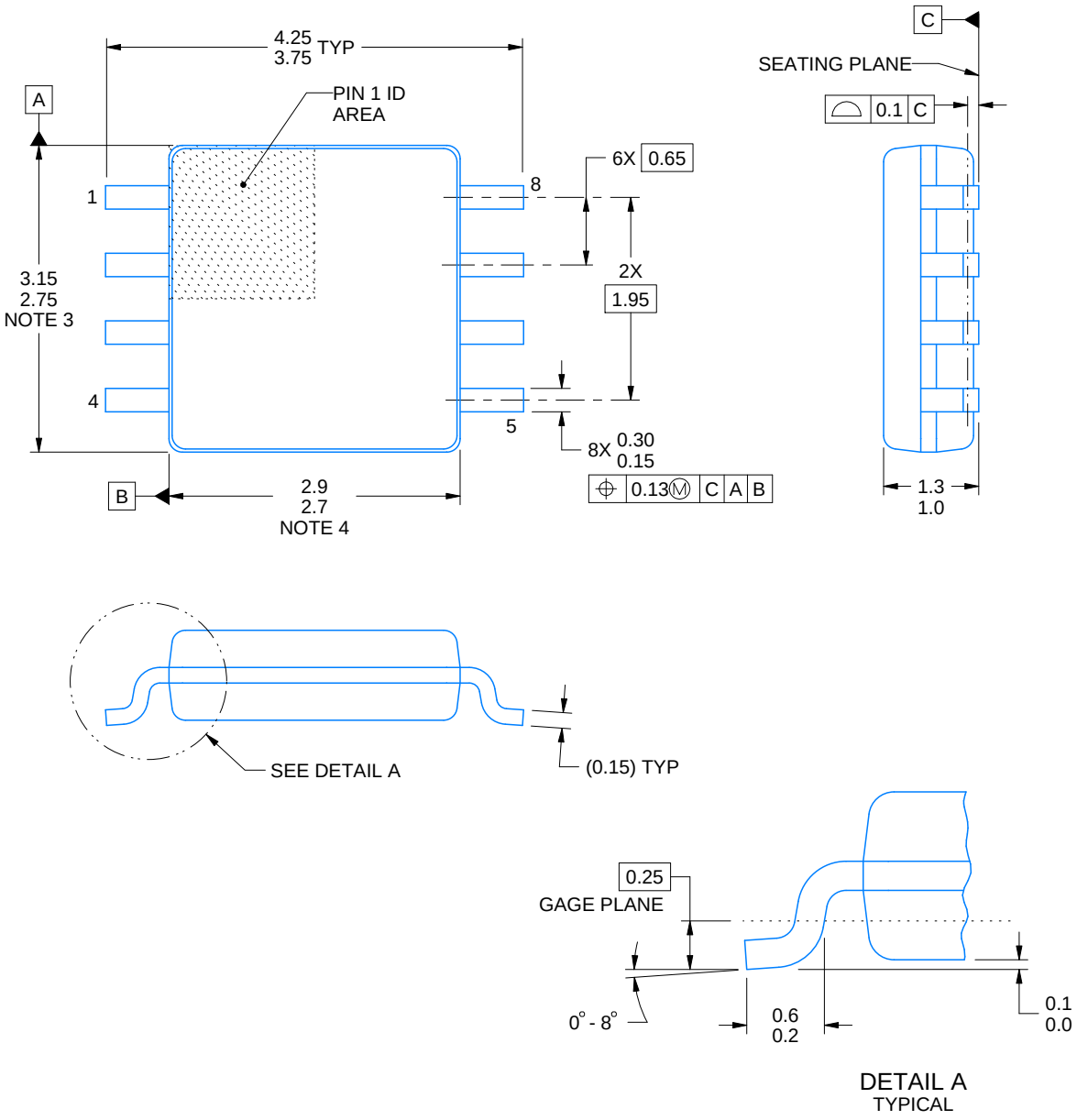
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2T45DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2T45DCTT	SM8	DCT	8	250	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2T45DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2T45DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.25	3.4	1.0	4.0	8.0	Q3
SN74LVC2T45DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2T45DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2T45YZPR	DSBGA	YZP	8	3000	180.0	8.4	1.02	2.02	0.63	4.0	8.0	Q1
SN74LVC2T45YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



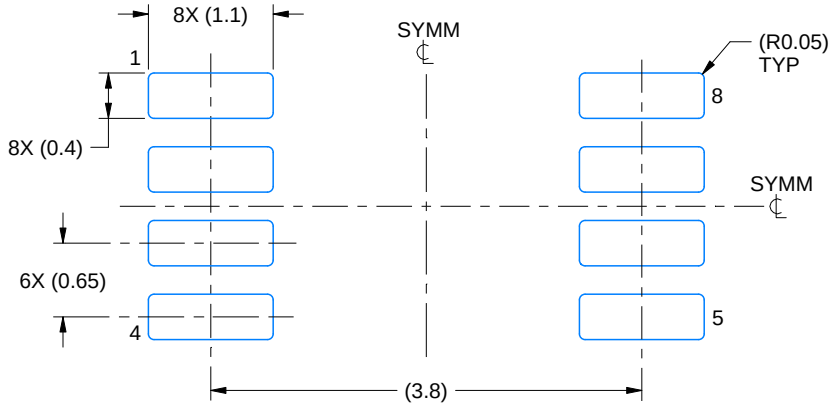
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2T45DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2T45DCTT	SM8	DCT	8	250	182.0	182.0	20.0
SN74LVC2T45DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC2T45DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
SN74LVC2T45DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2T45DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2T45YZPR	DSBGA	YZP	8	3000	182.0	182.0	20.0
SN74LVC2T45YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

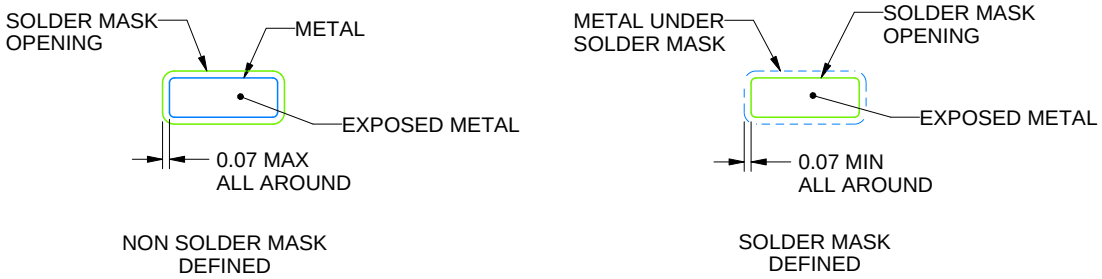


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MS-187.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

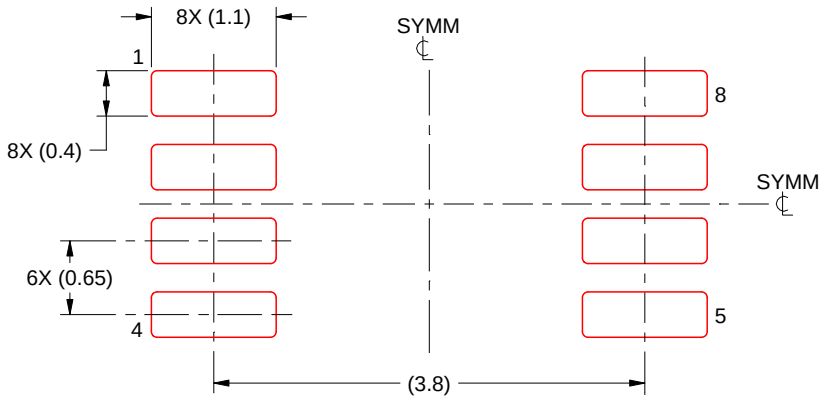


SOLDER MASK DETAILS

4220784/B 07/2020

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4220784/B 07/2020

NOTES: (continued)

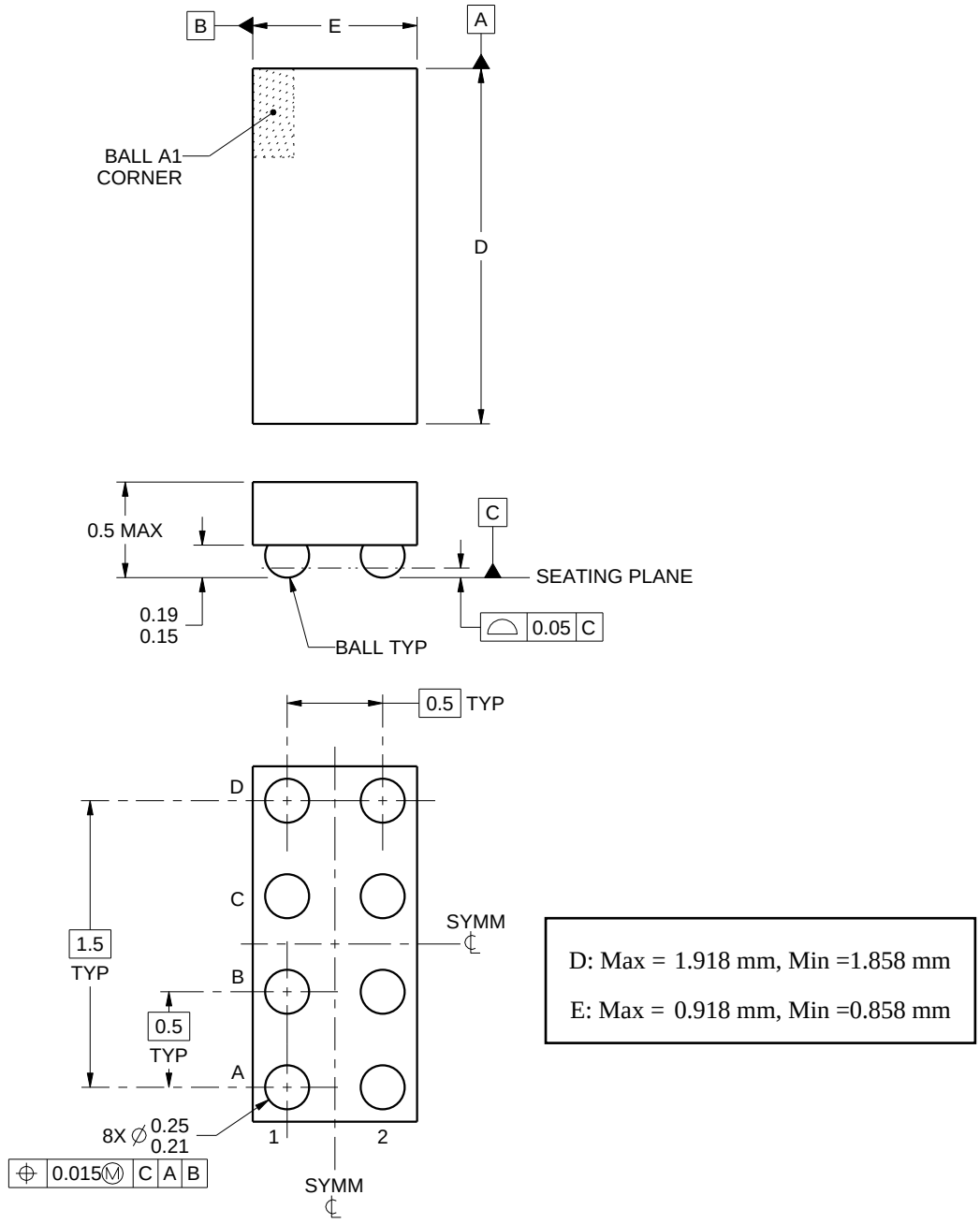
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

YZP0008

DSBGA - 0.5 mm max height

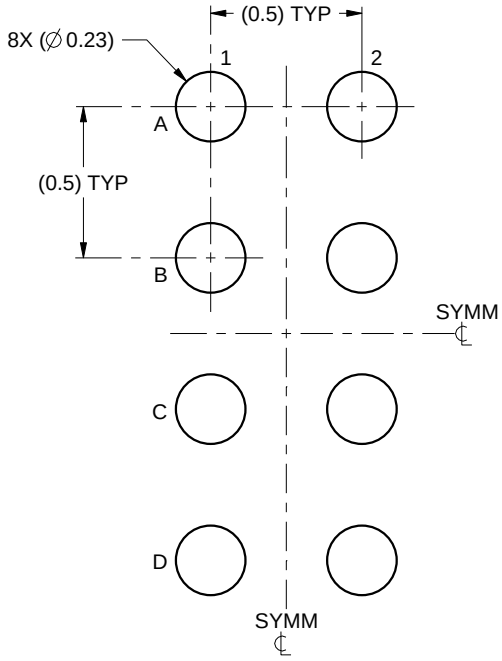
DIE SIZE BALL GRID ARRAY



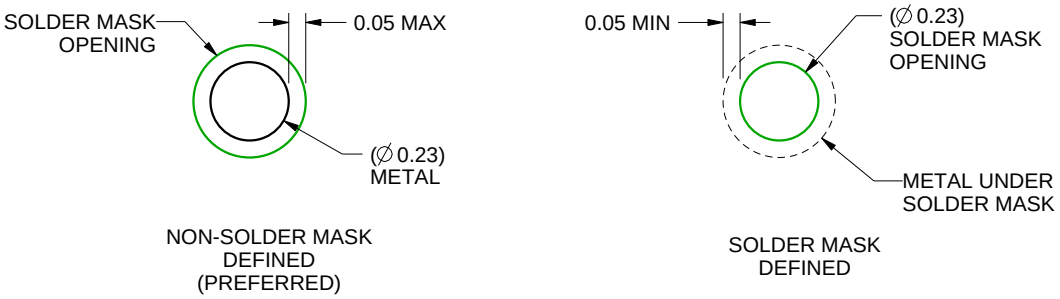
4223082/A 07/2016

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE:40X

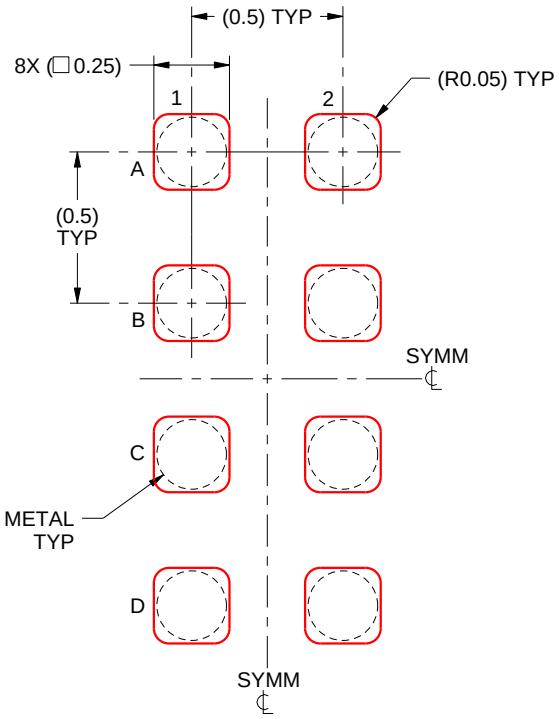


SOLDER MASK DETAILS
NOT TO SCALE

4223082/A 07/2016

NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



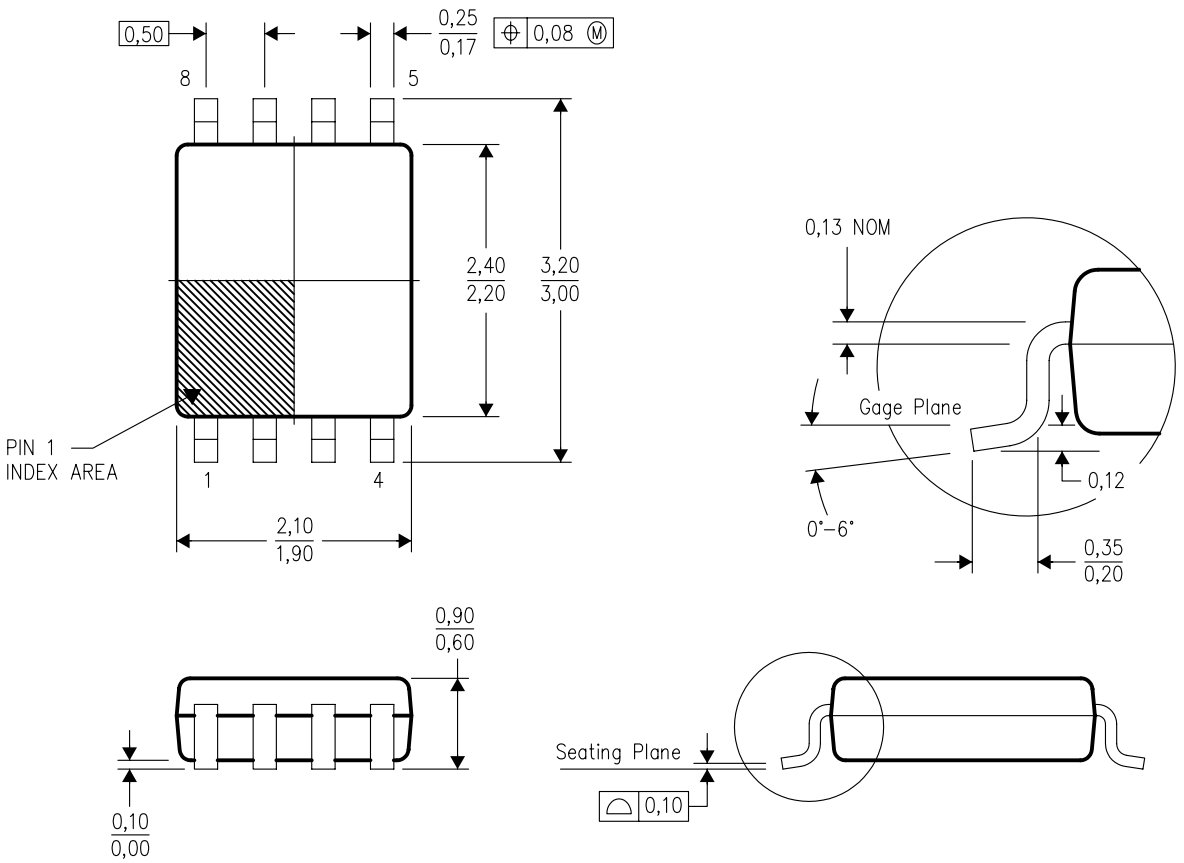
SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4223082/A 07/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

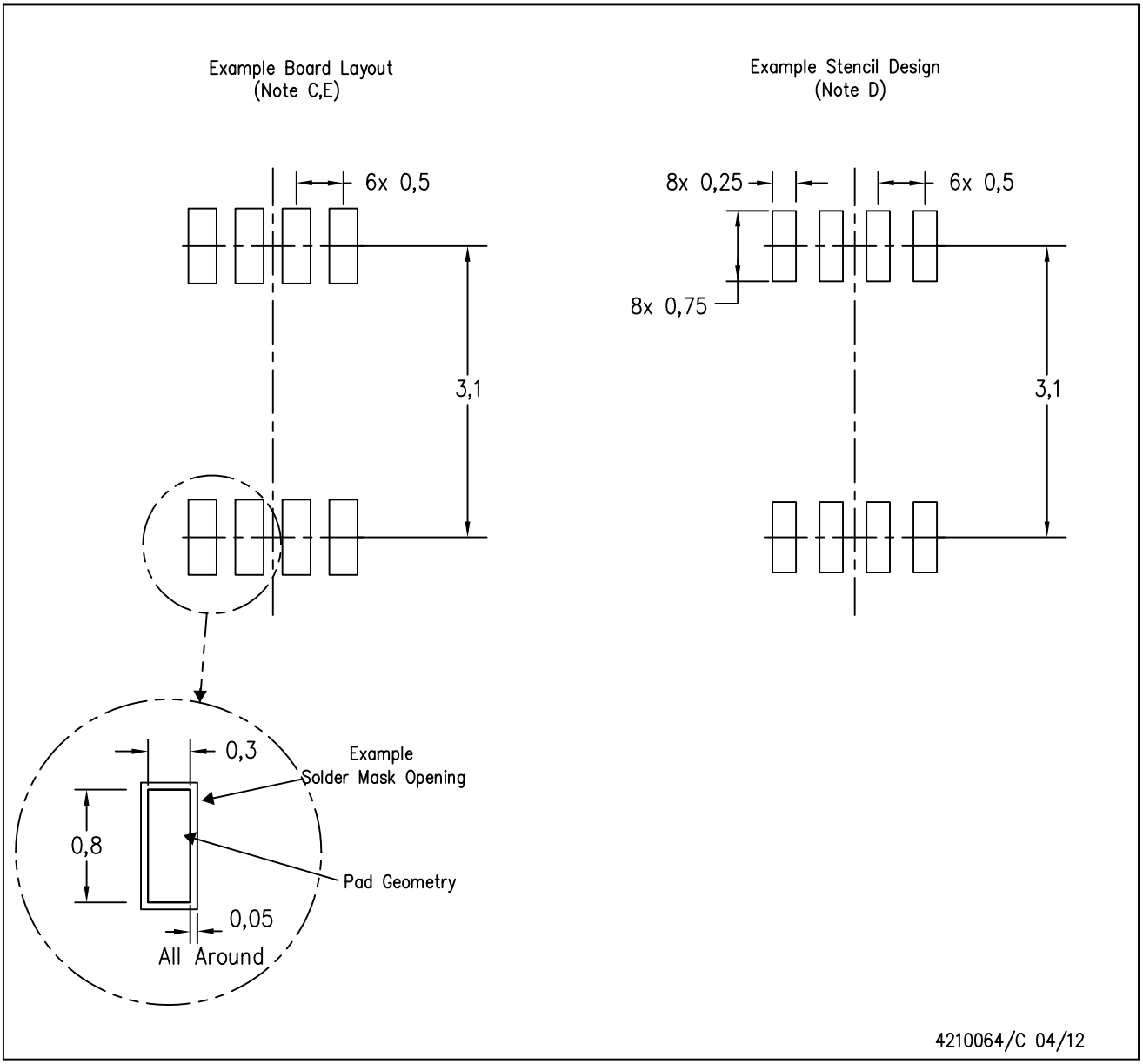
DCU (R–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE (DIE DOWN)



4200503/F 07/05

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–187 variation CA.

DCU (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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